

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20220802000.1

Qualification of new Fab site (FFAB) using qualified Process Technology, Die Revision, and additional Assembly, Datasheet & BOM option for select devices

Change Notification / Sample Request

Date: August 03, 2022

To: PREMIER FARNELL PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) process.

TI requires acknowledgement of receipt of this notification within 30 days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If samples or additional data are required, requests must be received within 30 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 30 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

This particular PCN is related to TI's multiyear transition plan for our two remaining factories with 150-millimeter production (DFAB in Dallas, Texas, and SFAB in Sherman, Texas). DFAB will remain open, but will focus on 200-mm production, with a smaller set of technologies. SFAB will close no earlier than 2024 and no later than 2025. As referenced in the "reason for change" below, these changes are part of our multiyear plan to transition these products to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the PCN Team (PCN www admin team@list.ti.com). For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

PCN Team SC Business Services

20220802000.1 Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE INA128U

CUSTOMER PART NUMBER

null

Technical details of this Product Change follow on the next page(s).

PCN Number: 20220802					PCN Date:		te:	August 03, 2022	
Title: Qualification of new			w Fa	w Fab site (FFAB) using qualified Process Technology, Die Revision,					
and additional Ass				mbly, Datasheet & BOM options for select devices					ices
Cus	tomer Contact	:	PCN	<u>l Manager</u>		Dept:			Quality Services
Proposed 1 st Ship Date:		Oct 31, 2022 Sample accepte		Requests ed until:		S	Sept 3, 2022*		
*Sa	imple requests	received	a fte	r Sept 3, 2022 wi	II not be	e su	ppo	rted.	
Cha	ange Type:								
	Assembly Site		\boxtimes	Assembly Process			\boxtimes	Assembly Materials	
\boxtimes	Design		\boxtimes	Electrical Specification	ation			Mechanical Specification	
	Test Site			☐ Packing/Shipping/Labeling				Test Process	
	Wafer Bump Sit	e	☐ Wafer Bump Material				Wafer Bump Process		
\boxtimes	Wafer Fab Site		☐ Wafer Fab Materials		ıls		\boxtimes	Wafei	Fab Process
			☐ Part number change						
	DCN Details								

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of a new fab & process technology (FFAB, BICOM3XHV) die revision, and Assembly & BOM option for selected devices as listed below in the product affected section. Construction differences are noted below:

C	urrent Fab Site)	Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
SFAB	JI1	150 mm	FFAB	BICOM3XHV	200 mm

The die was also changed as a result of the process change.

Additionally, there will be a BOM/Assembly options introduced for these devices in Group 1 below:

	MLA Current	MLA Alternate
Bond wire composition, diameter	Au, 1.2 mils	Cu, 1.0 mil
Mold Compound	4209640	4226323
Mount Compound	4205846	4147858

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The link to the revised datasheet is available in the table below.

Adde	ted the number	ring format for tak	alaa figuraa and	areas references throughout the decument				
	1.1			cross-references throughout the document				
- non				S				
	Changed Applications to link to latest end-equipment solutions on ti.com							
				ım Ratings				
				n <i>Absolute Maximum Ratings</i> refers to short-circuit to				
$V_S/2$	V _S / 25							
	Added single supply specification to Recommended Operating Conditions5							
Cona	litions			ation from V – 2 to (V–) + 2 in Recommended Operating				
Cond	litions							
				Operating Conditions				
				otherwise noted" conditions in <i>Electrical</i>				
Chan	nged test condit	tion for offset volta	age drift specifica	ation in <i>Electrical Characteristics</i> from "T _A = T _{MIN}				
Chan	ged typical long	g-term stability sp	pecification from	±0.1±3/G μV/mo to ±0.2±3/G μV/mo in <i>Electrical</i>				
				·/–) + 2 V minimum and (V+) − 2 V minimum across two				
				n across one row in <i>Electrical Characteristics</i>				
				in Electrical Characteristics				
				e specification in <i>Electrical Characteristics</i> for clarity				
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Adde	d test condition	n of "T _A = –40°C t	to +85°C" to inpu	t offset current drift specification in Electrical				
	•	•		6				
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Changes from Revision E (April 2019) to Revision F (May 2022)

%253Dsearch-

everything%2526usecase%253DGPN

Page

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-milimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☑ No Change	☑ No Change	☑ No Change	☑ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

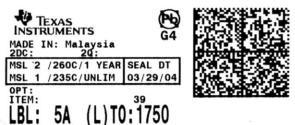
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
FFAB	FRE	DEU	Freising

Die Rev:

Current New

Die Rev [2P]	Die Rev [2P]
Е	A

Sample product shipping label (not actual product label)



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483812 (P) (2P) REV: (V) 0033317 (20L) 690: SHE (21L) CCO-USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:						
Group 1 Device lis	st (Wafer fab, die revision	, BOM and Datasheet ch	anges)			
INA128U	INA128UAE4	INA129U/2K5	INA128U/2K5G4			
INA129U	INA128UAG4	INA128UA/2K5	INA128UA/2K5E4			
INA128UA	INA129UAE4	INA129UA/2K5	INA128UA/2K5G4			
INA129UA	INA128U/2K5	INA128U-2/2K5	INA129UA/2K5G4			
INA128UG4						
Group 2 Device list (Datasheet changes only)						
INA128P	INA128PA	INA128PG4	INA129PG4			
ΤΝΔ129P	ΙΝΔ129ΡΔ					

For alternate parts with similar or improved performance, please visit the product page on $\overline{\text{TI.com}}$



TI Information Selective Disclosure

Qualification Report

Approve Date 01-Apr-2022

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: INA128U	QBS Process Reference: <u>INA828ID</u>	QBS Package Reference: <u>INA849D</u>
HTOL	Life Test, 100C ^A	300 Hours	-	-	1/77/0
HTOL	Life Test, 150C	300 Hours	-	3/231/0	-
HBM	ESD - HBM	2000 V	1/3/0	1/3/0	1/3/0
CDM	ESD - CDM	1000 V	1/3/0	1/3/0	1/3/0
LU	Latch-up	JEDEC78	1/6/0	1/6/0	1/6/0
ED	Electrical Characterization	Per Datasheet Parameters	1/30/0	3/90/0	1/30/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0	-
HBM	ESD - HBM	2000 V	1/3/0	1/3/0	1/3/0
HTSL	High Temp Storage Bake 170C	420 Hours	-	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	3/231/0
THB	Biased Temperature and Humidity, 85C/85%RH	1000 Hours	-	-	3/231/0
UHAST	Unbiased HAST 130C/85%RH	96 Hours	-	3/231/0	3/231/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/ Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green A Tj of device at 150C

Change Number: C2011216 TI Qualification ID: 20201124-137263

- QBS: Qual By Similarity
- Qual Device INA128U is qualified at LEVEL2-260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green



TI Information **Selective Disclosure**

Qualification Report

Approve Date 01-Apr-2022

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: <u>INA129U</u>	QBS Product Reference: <u>INA128U</u>	QBS Process Reference: <u>INA828ID</u>	QBS Package Reference: <u>INA849D</u>
HTOL	Life Test, 100C A	300 Hours	-	-	-	1/77/0
HTOL	Life Test, 150C	300 Hours	-	-	3/231/0	-
HBM	ESD - HBM	2000 V	-	1/3/0	1/3/0	1/3/0
CDM	ESD - CDM	1000 V	-	1/3/0	1/3/0	1/3/0
LU	Latch-up	JEDEC78	-	1/6/0	1/6/0	1/6/0
ED	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	3/90/0	1/30/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	-
HTSL	High Temp Storage Bake 170C	420 Hours	-	-	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	-	-	3/231/0	3/231/0
ТНВ	Biased Temperature and Humidity, 85C/85%RH	1000 Hours	-	-	-	3/231/0
UHAST	Unbiased HAST 130C/85%RH	96 Hours	-	-	3/231/0	3/231/0
YLD	FTY and Bin Summary	-	1/Pass	-	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles
 Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

ATj of device at 150C

TI Qualification ID: 20210624-140661

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN www admin_team@list.ti.com

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